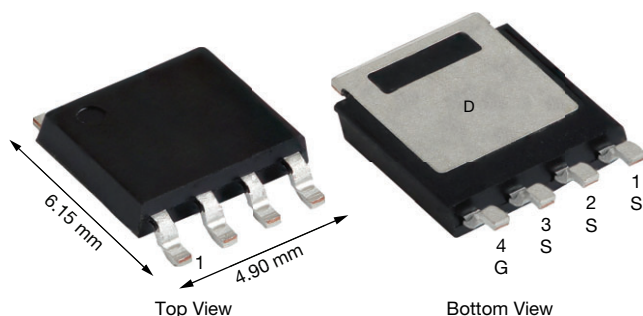


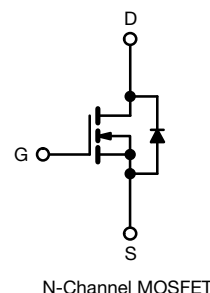
Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PowerPAK® SO-8L


FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE


N-Channel MOSFET

PRODUCT SUMMARY

V_{DS} (V)	60
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.0029
I_D (A)	293
Configuration	Single
Package	PowerPAK SO-8L

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	60	V
Gate-source voltage	V_{GS}	± 20	V
Continuous drain current	I_D	$T_C = 25$ °C ^a	293
		$T_C = 125$ °C	169
Continuous source current (diode conduction) ^a	I_S	454	A
Pulsed drain current ^b	I_{DM}	335	A
Single pulse avalanche current	I_{AS}	52	A
Single pulse avalanche energy	E_{AS}	135	mJ
Maximum power dissipation	P_D	$T_C = 25$ °C	500
		$T_C = 125$ °C	166
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^d		260	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient	R_{thJA}	42	°C/W
Junction-to-case (drain)	R_{thJC}	0.30	°C/W

Notes

- Package limited
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA		60	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.5	3.0	3.5	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	250	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	30	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 15 A	-	0.00235	0.0029	Ω
		V _{GS} = 10 V	I _D = 15 A, T _J = 125 °C	-	-	0.0049	
		V _{GS} = 10 V	I _D = 15 A, T _J = 175 °C	-	-	0.0060	
Forward transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 10 A		-	23	-	S
Dynamic ^b							
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	4365	6111	pF
Output capacitance	C _{oss}			-	1828	2560	
Reverse transfer capacitance	C _{rss}			-	53	75	
Total gate charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 30 V, I _D = 40 A	-	54	81	nC
Gate-source charge ^c	Q _{gs}			-	21	-	
Gate-drain charge ^c	Q _{gd}			-	4	-	
Gate resistance	R _g	f = 1 MHz		0.6	1.3	2.0	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 0.75 Ω I _D ≡ 40 A, V _{GEN} = 10 V, R _g = 1 Ω		-	17	26	ns
Rise time ^c	t _r			-	5	9	
Turn-off delay time ^c	t _{d(off)}			-	29	44	
Fall time ^c	t _f			-	4	8	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I _{SM}			-	-	335	A
Forward voltage	V _{SD}	I _F = 15 A, V _{GS} = 0 V		-	-	1.1	V
Body diode reverse recovery time	t _{rr}	I _F = 8 A, di/dt = 100 A/μs		-	50	100	ns
Body diode reverse recovery charge	Q _{rr}			-	52	104	nC
Reverse recovery fall time	t _a			-	22	-	ns
Reverse recovery rise time	t _b			-	29	-	
Body diode peak reverse recovery current	I _{RM(REC)}			-	1.8	-	A

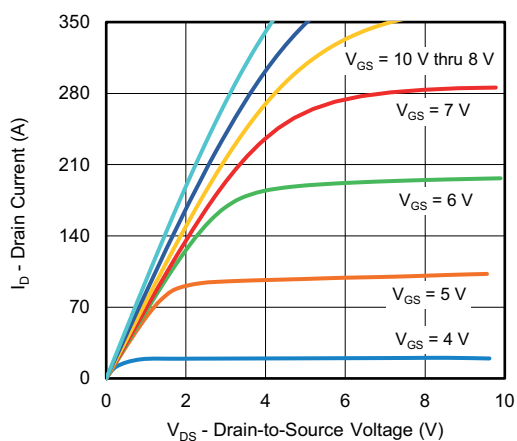
Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

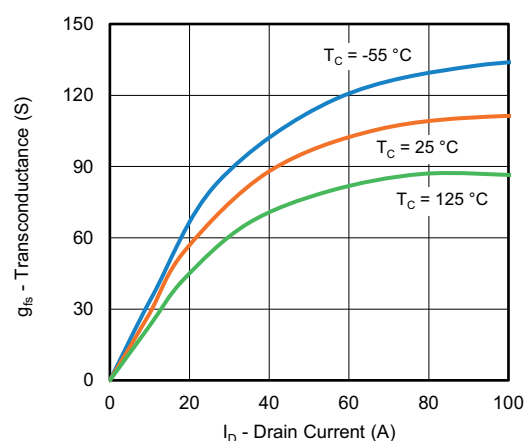
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



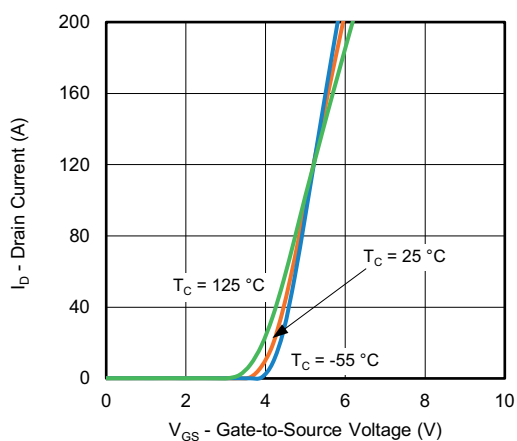
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



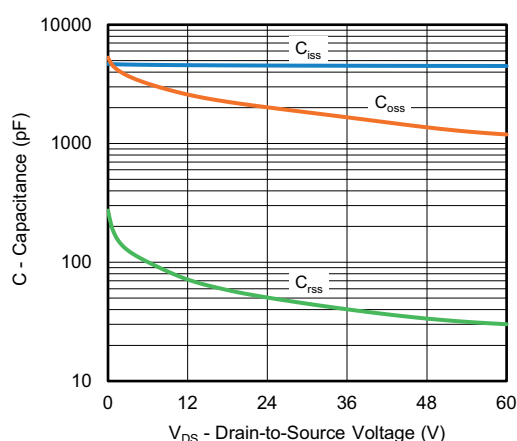
Output Characteristics



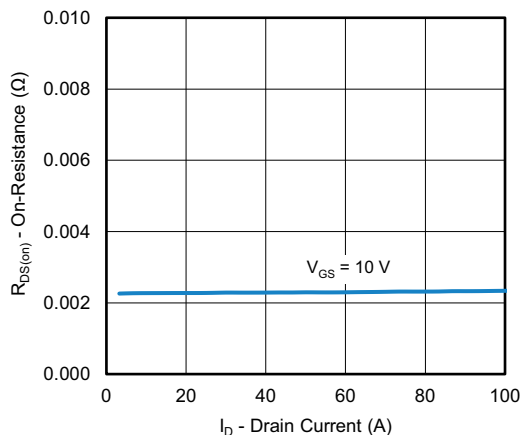
Transconductance



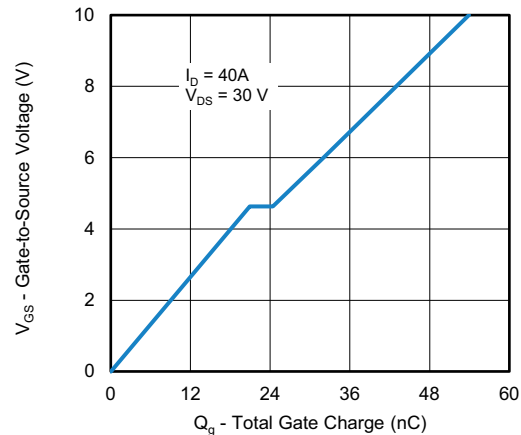
Transfer Characteristics



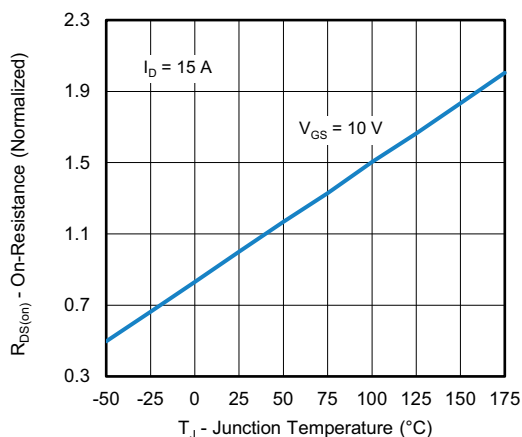
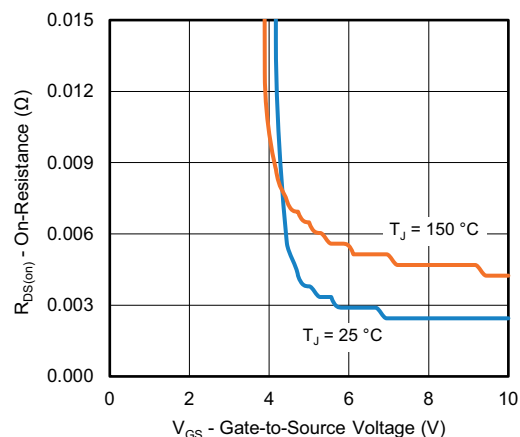
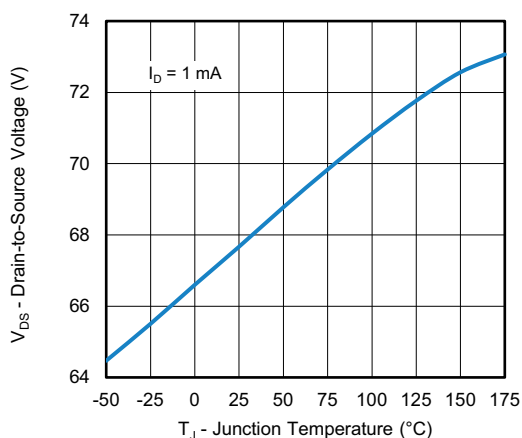
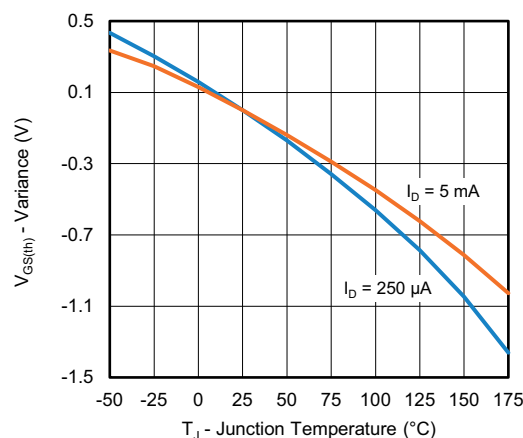
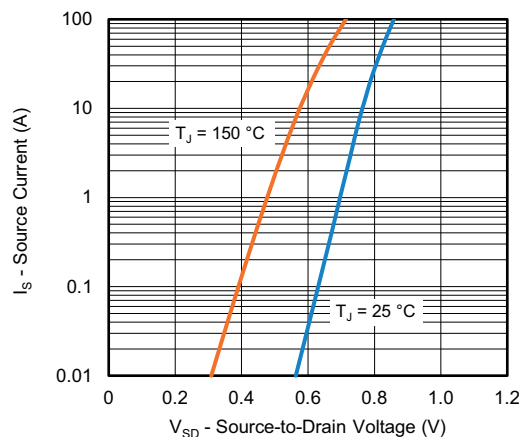
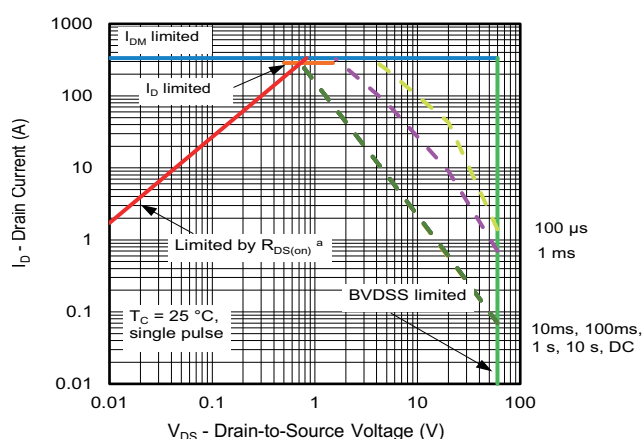
Capacitance



On-Resistance vs. Drain Current



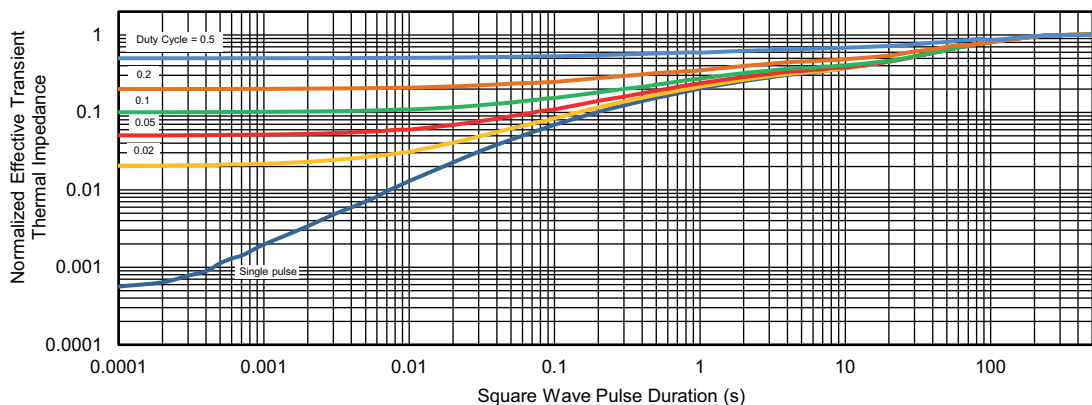
Gate Charge

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

On-Resistance vs. Junction Temperature

On-Resistance vs. Gate-to-Source Voltage

Drain Source Breakdown vs. Junction Temperature

Threshold Voltage

Source Drain Diode Forward Voltage

Safe Operating Area
Note

- $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



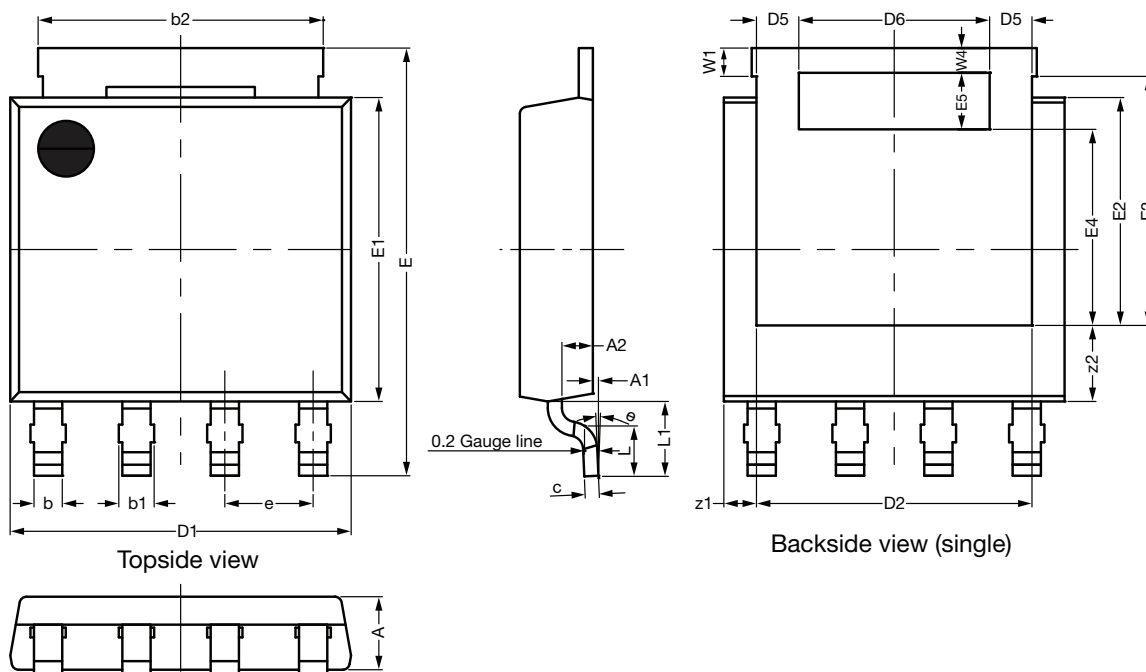
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63077.

PowerPAK® SO-8L Case Outline 3



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00	1.05	1.10	0.039	0.041	0.043
A1	0.00	---	0.127	0.000	---	0.005
A2	0.40	0.45	0.50	0.016	0.018	0.020
b	0.33	0.41	0.49	0.013	0.016	0.019
b1	0.43	0.51	0.59	0.017	0.020	0.023
b2	4.00	4.10	4.20	0.157	0.161	0.165
c	0.15	0.20	0.25	0.006	0.008	0.010
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D5	0.51	0.61	0.71	0.020	0.024	0.028
D6	2.64	2.74	2.84	0.104	0.108	0.112
e	1.27 BSC			0.050 BSC		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	3.18	3.28	3.38	0.125	0.129	0.133
E3	3.48	3.58	3.68	0.137	0.141	0.145
E4	2.72	2.82	2.92	0.107	0.111	0.115
E5	0.71	0.81	0.91	0.028	0.032	0.036
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
W1	0.31	0.41	0.51	0.012	0.016	0.020
W4	0.31	0.36	0.41	0.012	0.014	0.016
z1	0.37	0.47	0.57	0.015	0.019	0.022
z2	0.99	1.09	1.19	0.039	0.043	0.047
θ	0°	---	5°	0°	---	5°

ECN: S19-0643-Rev. B, 05-Aug-2019

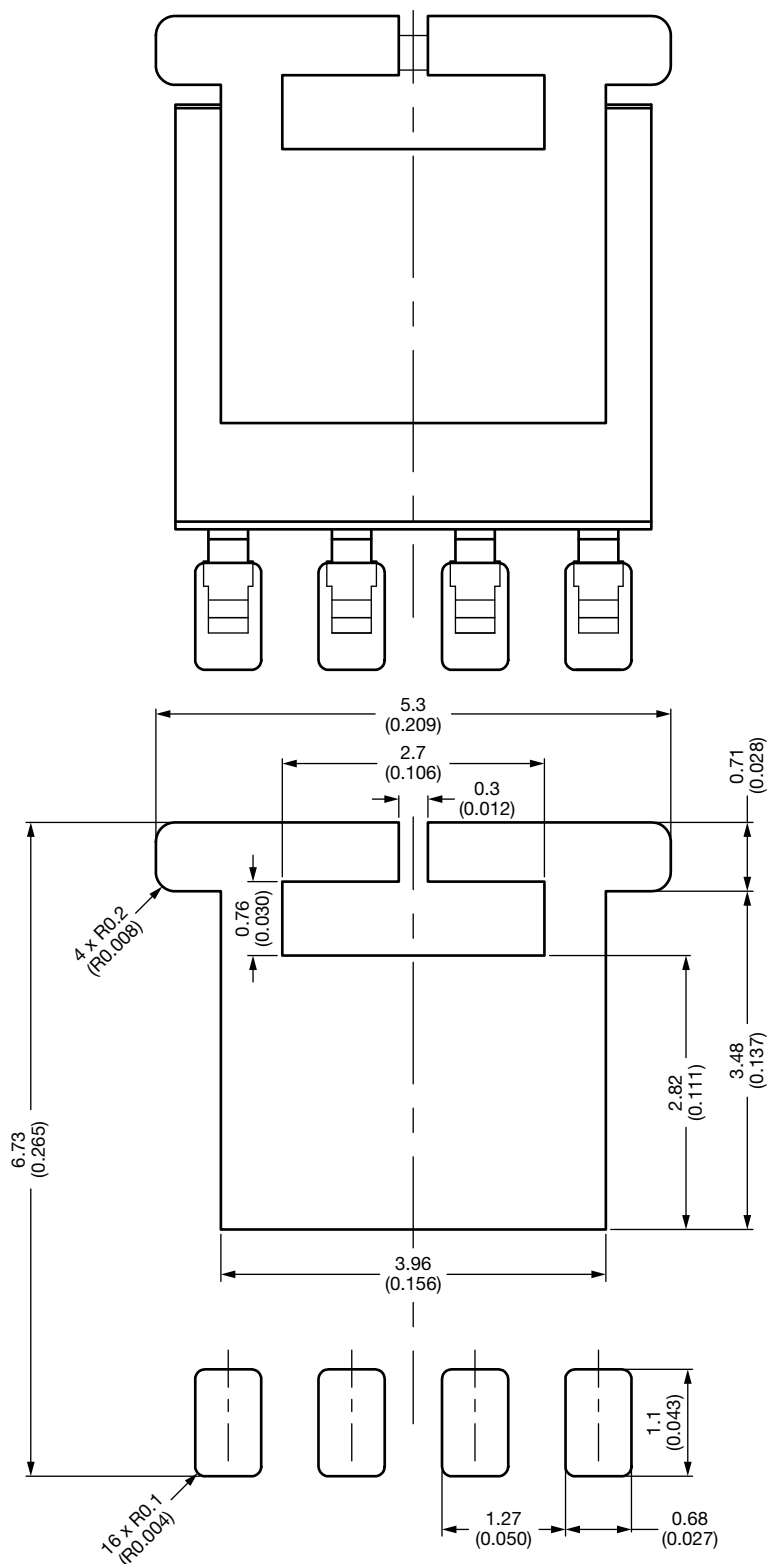
DWG: 6067

Note

- Millimeter will govern



Recommended Land Pattern PowerPAK® SO-8L Single Short Ear



Dimensions in Millimeters (Inches)



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